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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/634174
Filing Date	August 5, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2826 2823
Examiner Name	Tran, Tan J. Garcia

Sheet 1 of 7

Attorney Docket No: 1303.102US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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JAG	US20020070421	06/13/2002	Ashburn, Stanton P.	257	510	02/08/2002
JAG	US20020175330	11/28/2002	Geusic, Joseph			
JAG	US20020185686	12/12/2002	Christiansen, Silke H., et al.	257	347	04/03/2002
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EXAMINER

Joanne A. Garcia

DATE CONSIDERED

July 22, 2004

Substitute Disclosure Statement Form (PTO-1449)

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Attorney Docket No: 1303.102US1

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁴
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EXAMINER

Joanne A. Garcia

DATE CONSIDERED

July 22, 2004

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Sheet 4 of 7

Attorney Docket No: 1303.102US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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EXAMINER

Juanita A. Garcia

DATE CONSIDERED

July 22, 2004

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	Group Art Unit	2826 2823
	Examiner Name	Tren, Tan J. Garcia
Sheet 5 of 7	Attorney Docket No: 1303.102US1	

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EXAMINER

Joanne F. Garcia

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Sheet 6 of 7	Attorney Docket No: 1303.102US1	

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EXAMINER

Joannice A. Smith

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EXAMINER

Joanna A. Garcia

DATE CONSIDERED

July 29 2004

Substitute Disclosure Statement Form (PTO-1449)

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